

What is claimed is:

1. A method of forming a dummy wafer comprising:  
forming a masking film that covers a rear surface of a silicon wafer;  
spray coating aluminum on a front surface of the silicon wafer and thereby forming an aluminum film;  
spray coating a covering material on the aluminum film so that the aluminum film is completely covered and thereby forming a covering film; and  
removing the masking film.
2. A method of forming a dummy wafer as set forth in claim 1:  
wherein the covering film is selected from a ceramic film and a carbon film.
3. A method of forming a dummy wafer as set forth in claim 2:  
wherein an end portion of the aluminum film is covered with a ceramic film.
4. A method of forming a dummy wafer as set forth in claim 2:  
wherein the ceramic film is a film of aluminum oxide.
5. A method of forming a dummy wafer as set forth in claim 2:  
wherein the covering film has a film thickness distribution.

6. A method of forming a dummy wafer comprising:  
polishing a surface of a wafer that is made of aluminum;  
applying anodic oxidation to the surface of the wafer  
and thereby forming a film of aluminum oxide; and  
applying mirror polishing to a rear surface of the wafer.

7. A method of forming a dummy wafer as set forth in  
claim 6:

wherein the mirror polishing is applied according to  
polishing.

8. A method of forming a dummy wafer as set forth in  
claim 6:

wherein the anodic oxidation is applied with an electrode  
attached to the rear surface and with a masking film partially  
formed on a portion other than the electrode.